DESCRIPTION

The MXN2283 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -2.5V. This device is suitable for use as a load switch or in PWM applications.

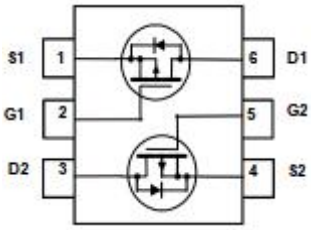
GENERAL FEATURES

- V_{DS}=-20V, I_D=-3.2A
  $R_{DS(ON)}$(Typ.)=140mΩ @ V_{GS}=-1.8V
  $R_{DS(ON)}$(Typ.)=95mΩ @ V_{GS}=-2.5V
  $R_{DS(ON)}$(Typ.)=68mΩ @ V_{GS}=-4.5V
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

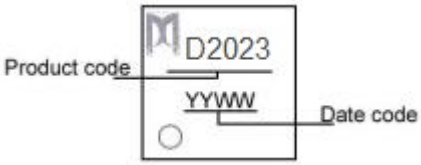
APPLICATION

- PWM applications
- Load switch
- Power management

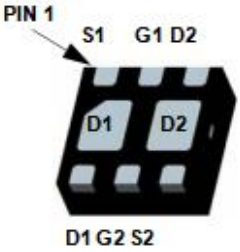
PINOUT



Schematic diagram



Marking and pin Assignment



DFN2X2-6L bottom view

ORDERING INFORMATION

Part Number	Marking	StorageTemperature	Package	Devices Per Reel
MXN2283	D2023	-55°C to 150°C	DFN2X2-6L	-

ABSOLUTE MAXIMUM RATINGS(T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	-3.2	A
Pulsed Drain Current(Note1)	I_{DM}	-10	A
Maximum Power Dissipation	P_D	1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE

Thermal Resistance, Junction-to-Ambient(Note2)	$R_{\theta JA}$	125	°C/W

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
Note 2. Surface Mounted on FR4 Board, t ≤ 10 sec.

ELECTRICAL CHARACTERISTICS(T_A=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=-250μA	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V, V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V, V_{DS}=0V	-	-	±100	nA
On Characteristics(Note3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-0.45	-0.7	-1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-1.8V, I_D=-1.7A	-	140	170	mΩ
		V_{GS}=-2.5V, I_D=-2.2A	-	95	120	mΩ
		V_{GS}=-4.5V, I_D=-2.8A	-	68	95	mΩ
Dynamic Characteristics(Note4)						
Input Capacitance	C_{iss}	V_{DS}=-10V, V_{GS}=0V, F=10KHz	-	405	-	pF
Output Capacitance	C_{oss}		-	75	-	pF
Reverse Transfer Capacitance	C_{rss}		-	55	-	pF
Switching Characteristics(Note4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-10V, I_D=-1A, V_{GS}=-4.5V, R_{GEN}=10Ω	-	11	-	nS
Turn-on Rise Time	t_r		-	35	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=-10V, I_D=-3A, V_{GS}=-2.5V	-	3.3	12	nC
Gate-Source Charge	Q_{gs}		-	0.7	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage(Note3)	V_{SD}	V_{GS}=0V, I_S=-1.3A	-	-	-1.2	V
Diode Forward Current(Note2)	I_S		-	-	-1.3	A

Note 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
Note 3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
Note 4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 1. Switching Test Circuit

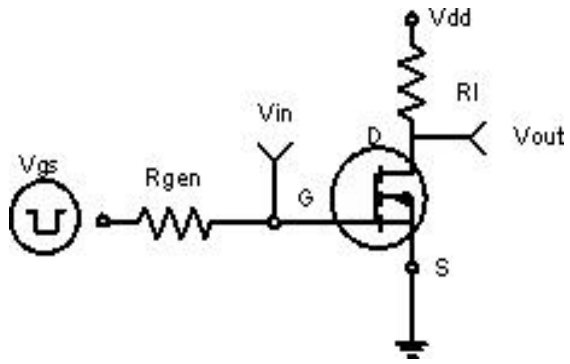


Figure 2. Switching Waveform

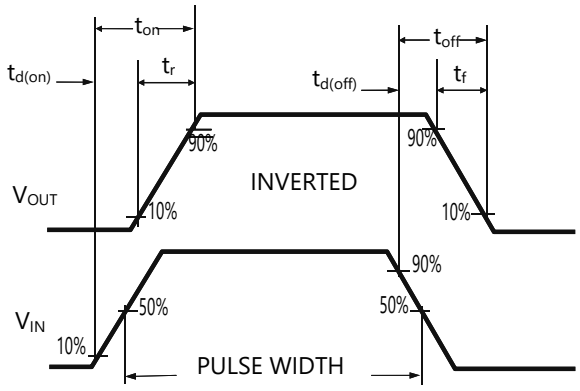


Figure 3. Power Dissipation

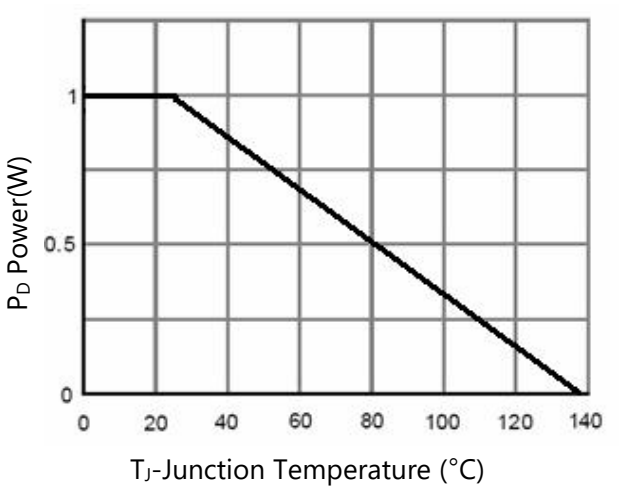


Figure 4. Drain Current

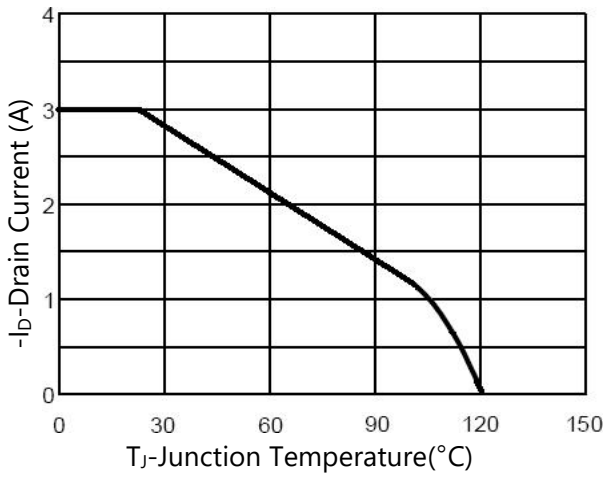


Figure 5. Output Characteristics

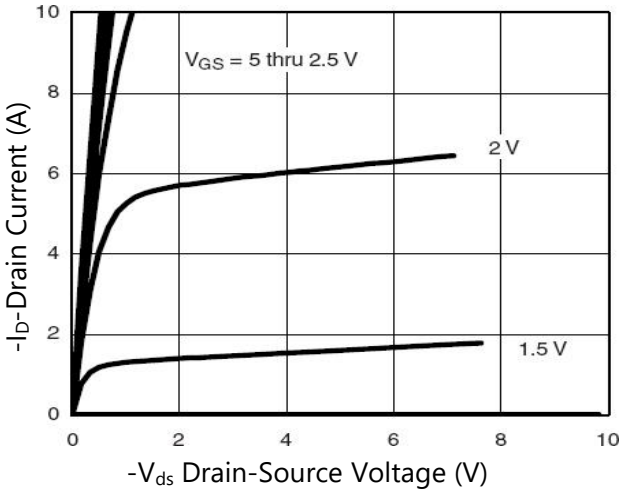
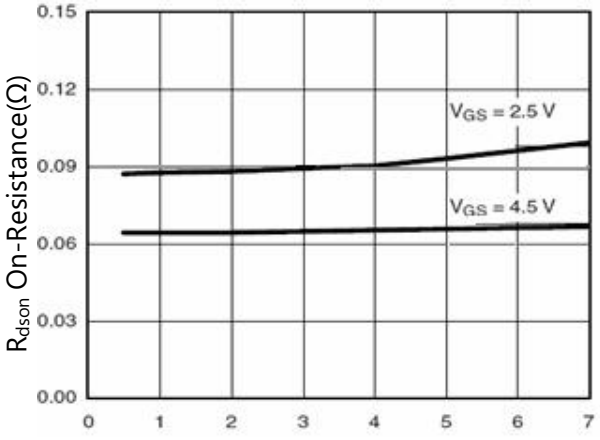


Figure 6. R_{dson} vs Drain Current



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7. Transfer Characteristics

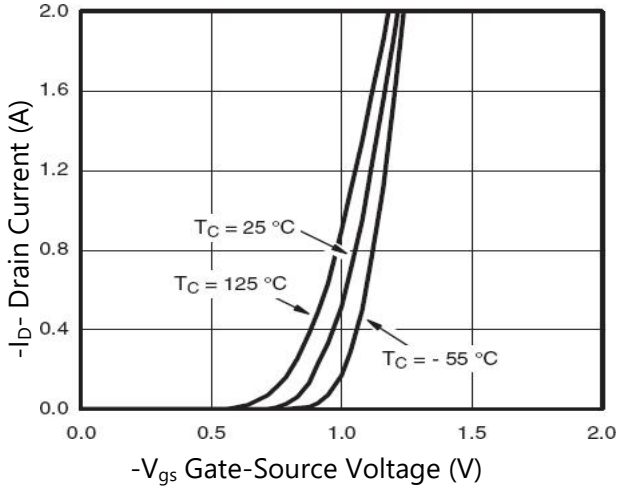


Figure 8. R_{dson} vs Junction Temperature

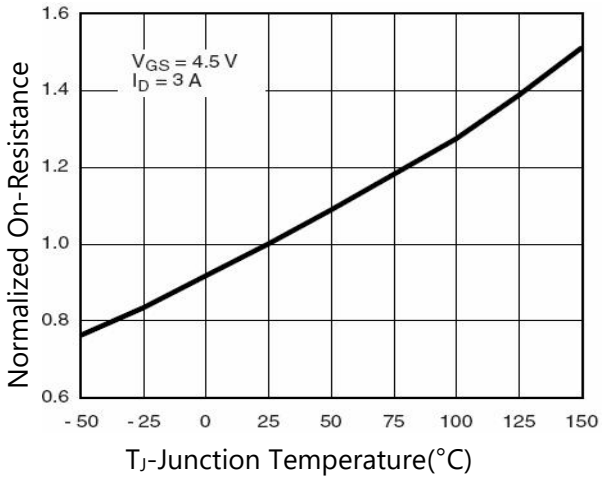


Figure 9. R_{dson} vs V_{gs}

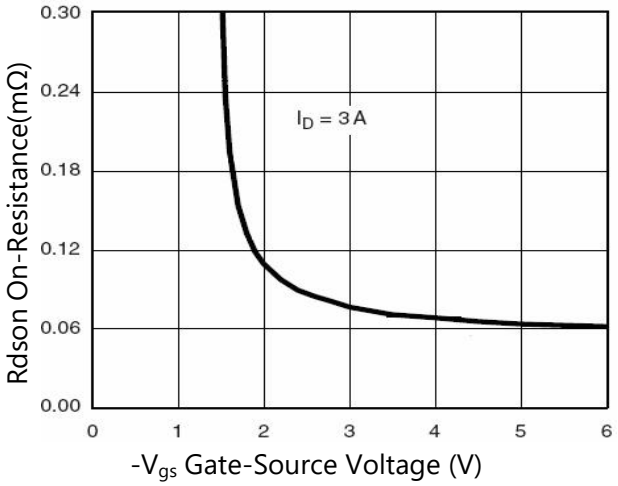


Figure 10. Capacitance vs V_{ds}

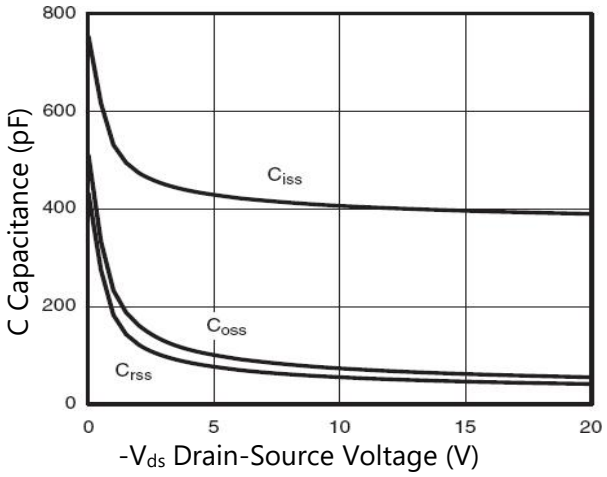


Figure 11. Gate Charge

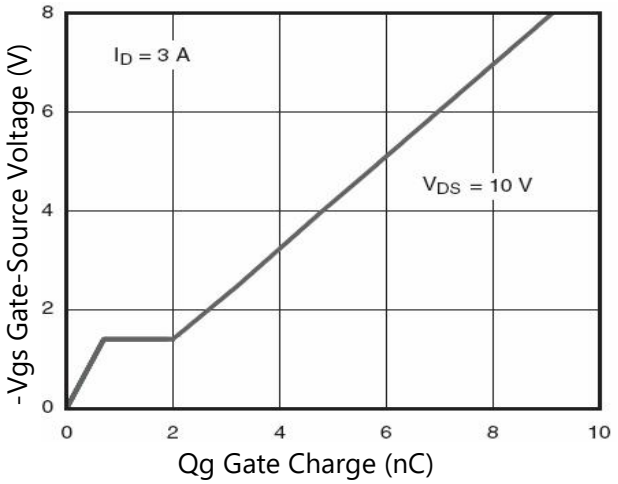
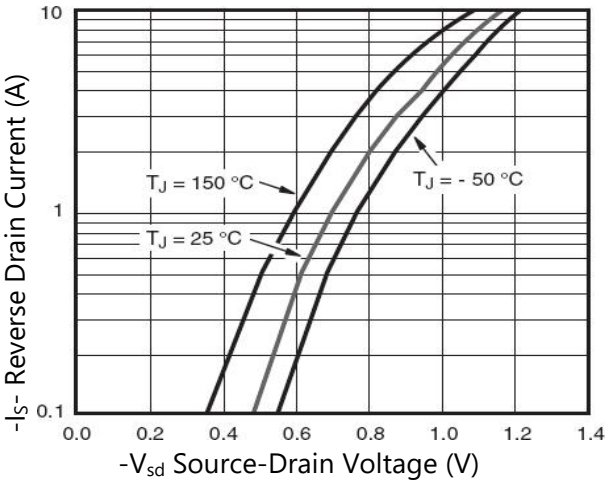


Figure 12. Source- Drain Diode Forward



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 13. Safe Operation Area

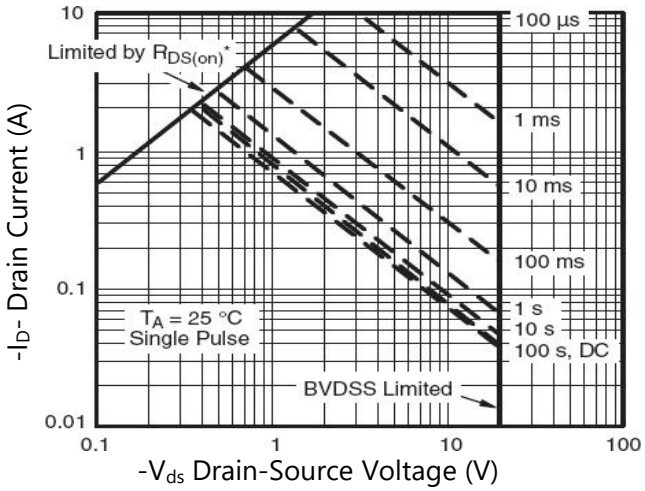
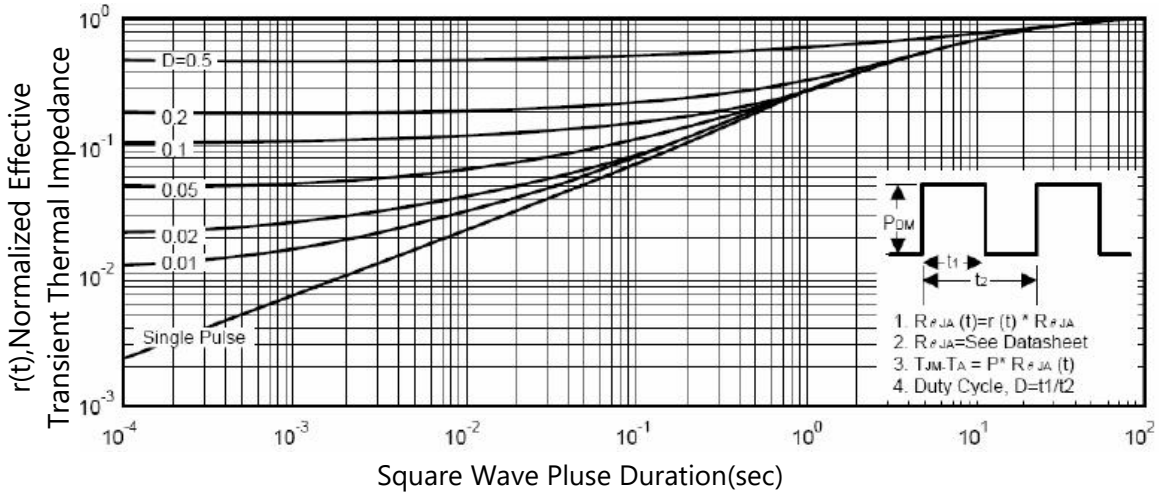
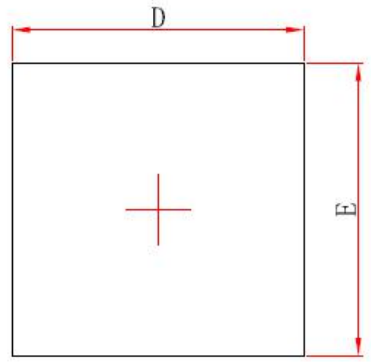


Figure 14. Normalized Maximum Transient Thermal Impedance

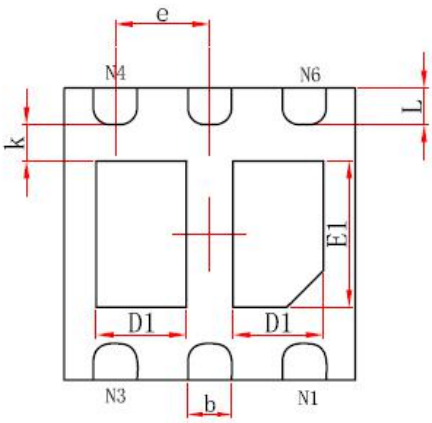


PACKAGE INFORMATION

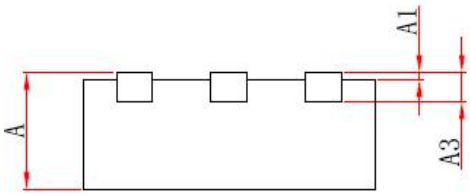
DFN2X2-6L



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700/0.800	0.800/0.900	0.028/0.031	0.031/0.035
A1	0.000	0.050	0.000	0.002
A3	0.203 REF.		0.008 REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.520	0.720	0.020	0.028
E1	0.900	1.100	0.035	0.043
k	0.200 MIN.		0.008 MIN.	
b	0.250	0.350	0.010	0.014
e	0.650 TYP.		0.026 TYP.	
L	0.174	0.326	0.007	0.013